

Quad 2-Input NOR Gate

MC74VHC02, MC74VHCT02A

The MC74VHC02 and MC74VHCT02A are high speed CMOS quad 2-input NOR gates fabricated with silicon gate CMOS technology. These achieve high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC02 inputs are compatible with standard CMOS levels while the MC74VHCT02A inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The MC74VHC02 and MC74VHCT02A internal circuits are composed of three stages, including a buffer output which provides high noise immunity and stable output. The input structures tolerate voltages up to $5.5~\rm V$, allowing the interface of $5~\rm V$ systems to $3~\rm V$ systems.

The MC74VHCT02A output structures provide protection when $V_{\rm CC}$ = 0 V. These output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: $t_{PD} = 3.6 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance:

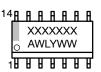
Human Body Model > 2000 V

- Chip Complexity: 40 FETs or 10 Equivalent Gates
- –Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



XXXXXX = Specific Device Code
A = Assembly Location

WL, L = Wafer Lot
 Y = Year
 WW, W = Work Week
 G or = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

Y1 [1 ●		v _{cc}
A1 [2	13	Y4
В1 [3	12] B4
Y2 [4	11] A4
A2 [5	10] Y3
B2 [6	9] B3
GND [7	8	_ A3

FUNCTION TABLE

Inp	uts	Output			
Α	A B				
L	L	Н			
L	Н	L			
H	L	L			
Н	Н	L			

ORDERING INFORMATION

See detailed ordering and shipping information on page 7 of this data sheet.

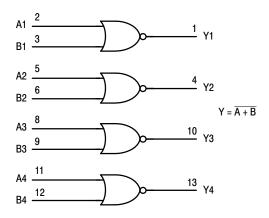


Figure 1. LOGIC DIAGRAM

MAXIMUM RATINGS

Symbol	Para	ameter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{in}	DC Input Voltage		-0.5 to +6.5	V
V _{out}	DC Output Voltage (MC74VHC)		-0.5 to V _{CC} + 0.5	V
	DC Output Voltage (MC74VHCT)	Active Mode (High or Low State) Tristate Mode (Note 1) Power-Off Mode ($V_{CC} = 0 V$)	-0.5 to V _{CC} + 0.5 -0.5 to +6.5 -0.5 to +6.5	
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, Per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±50	mA
I _{IK}	Input Clamp Current		-20	mA
I _{OK}	Output Clamp Current	MC74VHC MC74VHCT	±20 –20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 1	10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SOIC-14 QFN14 TSSOP-14	116 130 150	°C/W
P _D	Power Dissipation in Still Air at 25°C	SOIC-14 QFN14 TSSOP-20	1077 962 833	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	> 2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri-stated.

- Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
 HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
- Tested to EIA/JÉSD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	F	arameter	Min	Max	Unit
MC74VHC			•		
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	Output Voltage (Note 5)		0	V _{CC}	V
T _A	Operating Temperature		-55	+125	°C
t _r , t _f	Input Rise or Fall Rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$ $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0	100 20	ns/V
MC74VHC	- 				-
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage (Note 5)		0	5.5	V
V _{OUT}	DC Output Voltage (Note 5)	Active Mode (High or Low State) Tristate Mode Power-Off Mode ($V_{CC} = 0 V$)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Temperature		-55	+125	°C
t _r , t _f	Input Rise or Fall Rate	V _{CC} = 4.5 V to 5.5 V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (MC74VHC02)

			v _{cc}		T _A = 25°0	C	T _A = - 40	0 to 85°C	
Symbol	Parameter	Test Conditions	v	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		٧
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	٧
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ o r } V_{IL}$ $I_{OH} = -50 \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= - \text{ 4 mA} \\ I_{OH} &= - \text{ 8 mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μА
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			2.0		20.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{5.} Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

AC ELECTRICAL CHARACTERISTICS (MC74VHC02)

				T _A = 25°C		T _A = - 40		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Output Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.6 8.1	7.9 11.4	1.0 1.0	9.5 13.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.6 5.1	5.5 7.5	1.0 1.0	6.5 8.5	
C _{in}	Maximum Input Capacitance			4	10		10	pF

Ī			Typical @ 25°C, V _{CC} = 5.0 V	
	C_{PD}	Power Dissipation Capacitance (Note 6)	15	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

NOISE CHARACTERISTICS (MC74VHC02, $C_L = 50 \text{ pF}$, $V_{CC} = 5.0 \text{ V}$)

		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

DC ELECTRICAL CHARACTERISTICS (MC74VHTC02A)

			Vcc	1	T _A = 25°C		T _A ≤ 85°C		T _A ≤ 125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V _{IL}	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	٧
V _{OH}	Minimum High-Level Out- put Voltage V _{IN} = V _{IH} or V _{II}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	AIV = AIH OI AIF	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V _{OL}	Maximum Low-Level Out- put Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5			2.0		20		40	μΑ
I _{CCT}	Quiescent Supply Current	Input: V _{IN} = 3.4 V	5.5			1.35		1.50		1.65	mA
I _{OPD}	Output Leakage Current	V _{OUT} = 5.5 V	0.0			0.5		5.0		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (MC74VHTC02A)

Sym-			T _A = 25°C		$T_A \le 85^{\circ}C$		T _A ≤ 125°C			
bol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Max	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A or B to Y	$V_{CC} = 3.0 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.6 8.1	7.9 11.4		9.5 13.0		12.5 17.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.6 5.1	5.5 7.5		6.5 8.5		9.0 11.0	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF

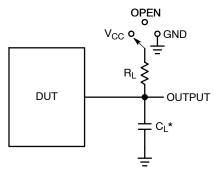
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Note 6)	20	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOISE CHARACTERISTICS (MC74VHTC02A, C_L = 50 pF, V_{CC} = 5.0 V)

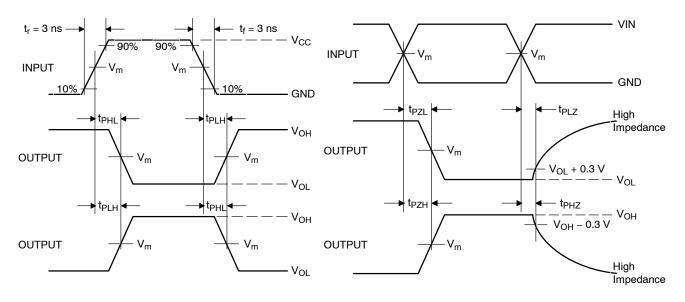
		T _A =	25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per gate). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C _L	R_L
t _{PLH} / t _{PHL}	Open	See AC Characteristics	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	Table	
t _{PHZ} / t _{PZH}	GND		

Figure 2. Test Circuit



Device	V _{IN} , V	V _m , V
MC74VHC02	V _{CC}	50% x V _{CC}
MC74VHCT02A	3 V	1.5 V

Figure 3. Switching Waveforms

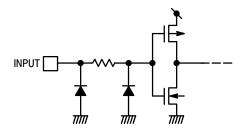


Figure 4. Input Equivalent Circuit

 $^{^{\}star}C_{L}$ Includes probe and jig capacitance

ORDERING INFORMATION

Device	Package	Marking	Shipping [†]
MC74VHC02DR2G	SOIC-14	VHC02G	2500 / Tape & Reel
MC74VHC02DTR2G	TSSOP-14	VHC 02	2500 / Tape & Reel
MC74VHC02DTR2G-Q*	TSSOP-14	VHC 02	2500 / Tape & Reel
MC74VHCT02ADR2G	SOIC-14	VHCT02AG	2500 / Tape & Reel
MC74VHCT02ADTR2G	TSSOP-14	VHCT 02A	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

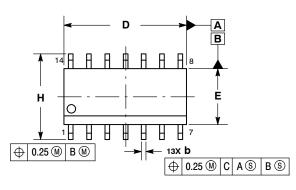


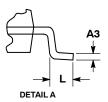


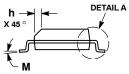
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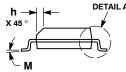
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





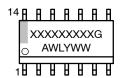




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE
 MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*

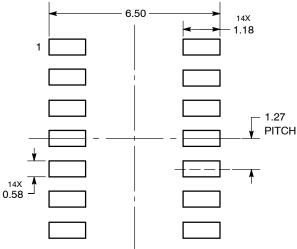


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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2X L/2

PIN 1 – IDENT.

L

△ 0.15 (0.006) T U S

△ 0.15 (0.006) T U S

☐ 0.10 (0.004) -T- SEATING



-V-

B

-U-

J J1

DETAIL E



0.25 (0.010)

DETAIL E

SECTION N-N

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

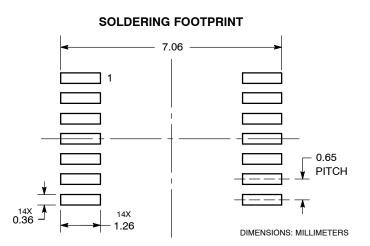
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		S INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С	-	1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
М	0	a o	0 °	Q°	

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot - Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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